



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92L Plastic-Encapsulate Transistors

KSC2330 TRANSISTOR (NPN)

FEATURE

Power dissipation

P_{CM} : 1 W ($T_{amb}=25^{\circ}C$)

Collector current

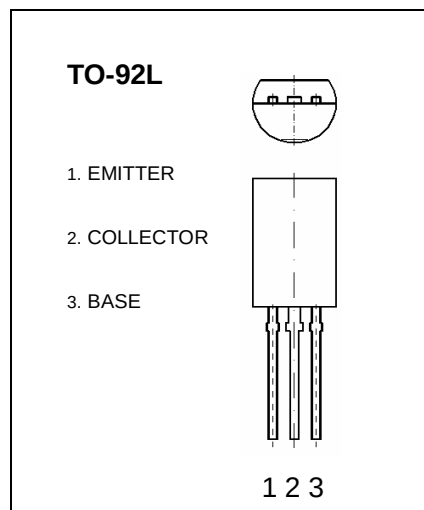
I_{CM} : 0.1 A

Collector-base voltage

$V_{(BR)CBO}$: 300 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	300		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=5mA, I_B=0$	300		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	7		V
Collector cut-off current	I_{CBO}	$V_{CB}=200V, I_E=0$		0.1	μA
DC current gain	h_{FE}	$V_{CE}=10V, I_C=20mA$	40	240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=1mA$		0.5	V
Transition frequency	f_T	$V_{CE}=30V, I_C=10mA$	50		MHz

CLASSIFICATION OF h_{FE}

Rank	R	O	Y
Range	40-80	70-140	120-240